

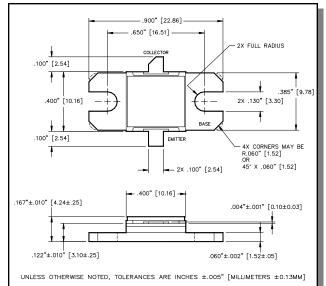
## **M/A-COM Products** Released, 10 Jul 07

# **Radar Pulsed Power Transistor** 30W, 3.1-3.4 GHz, 1µs Pulse, 10% Duty

#### Features

- NPN silicon microwave power transistors •
- Common base configuration
- Broadband Class C operation •
- High efficiency inter-digitized geometry •
- Diffused emitter ballasting resistors •
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- **RoHS** compliant

#### **Outline Drawing**



#### Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V <sub>CES</sub>	65	V
Emitter-Base Voltage	V <sub>EBO</sub>	3.0	V
Collector Current (Peak)	Ι <sub>C</sub>	3.6	А
Power Dissipation @ +25°C	P <sub>TOT</sub>	350	W
Storage Temperature	T <sub>STG</sub>	-65 to +200	°C
Junction Temperature	TJ	200	°C

### Electrical Specifications: T<sub>c</sub> = 25 ± 5°C (Room Ambient )

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA		$BV_{CES}$	65	-	V
Collector-Emitter Leakage Current	$V_{CE} = 40V$		I <sub>CES</sub>	-	1.5	mA
Thermal Resistance	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	R <sub>TH(JC)</sub>	-	0.5	°C/W
Input Power	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	P <sub>IN</sub>	-	5.33	W
Power Gain	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	G <sub>P</sub>	7.5	-	dB
Collector Efficiency	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	η <sub>c</sub>	35	-	%
Input Return Loss	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	RL	-	-6	dB
Load Mismatch Tolerance	Vcc = 36V, Pout = 30W	F = 3.25 GHz	VSWR-T	-	2:1	-

1

- ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed. PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology
- North America Tel: 800.366.2266 / Fax: 978.366.2266
- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298 Visit www.macomtech.com for additional data sheets and product information.

Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

M/A-COM Technology Solutions Inc. and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

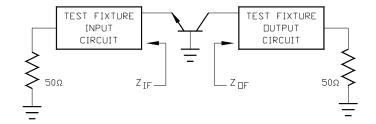


Radar Pulsed Power Transistor					
30W, 3.1-3.4 GHz, 1µs Pulse, 10% Duty					

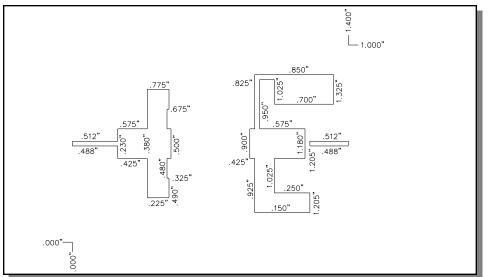
M/A-COM Products Released, 10 Jul 07

### **RF Test Fixture Impedance**

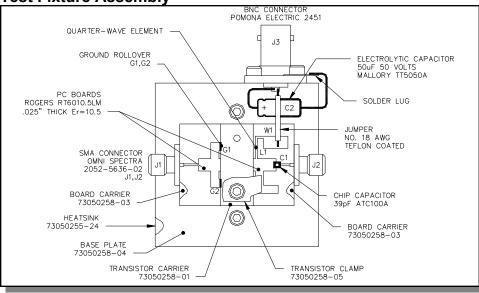
F (GHz)	Z <sub>IF</sub> (Ω)	Z <sub>OF</sub> (Ω)
3.10	16.0 + j5.0	19.0 + j3.0
3.25	14.5 + j2.0	15.5 - j2.0
3.40	11.5 + j0.0	10.0 - j3.5



#### **Test Fixture Circuit Dimensions**



#### **Test Fixture Assembly**



2

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed. **PRELIMINARY**: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- North America Tel: 800.366.2266 / Fax: 978.366.2266
- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
- Visit www.macomtech.com for additional data sheets and product information.

M/A-COM Technology Solutions Inc. and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.